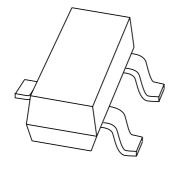
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BSS64**NPN high voltage transistor

Product specification Supersedes data of 2004 Jan 16 2004 Mar 12





# NPN high voltage transistor

**BSS64** 

#### **FEATURES**

- Low current (max. 100 mA)
- High voltage (max. 80 V).

#### **APPLICATIONS**

- High-voltage general purpose and switching applications
- Intended for thick and thin-film circuit applications.

#### **DESCRIPTION**

NPN transistor in a SOT23 plastic package. PNP complement: BSS63.

#### **MARKING**

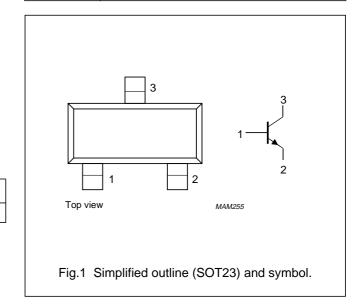
TYPE NUMBER	MARKING CODE <sup>(1)</sup>		
BSS64	60* or AM		

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE			
ITPE NOWIBER	NAME DESCRIPTION		VERSION		
BSS64	_	plastic surface mounted package; 3 leads SOT2			

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	120	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	250	mA
I <sub>BM</sub>	peak base current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

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# NPN high voltage transistor

**BSS64** 

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_j$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 90 V	_	_	100	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 90 V; T <sub>j</sub> = 150 °C	_	_	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	_	0.5	200	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 1 V	_	60	_	
		$I_C = 10 \text{ mA}; V_{CE} = 1 \text{ V}$	20	80	_	
		I <sub>C</sub> = 20 mA; V <sub>CE</sub> = 1 V	_	55	_	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = 4 \text{ mA}; I_B = 400 \mu\text{A}$	_	_	150	mV
	voltage	I <sub>C</sub> = 50 mA; I <sub>B</sub> = 15 mA	_	_	200	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = I <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	_	3	_	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 4 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	60	100	_	MHz

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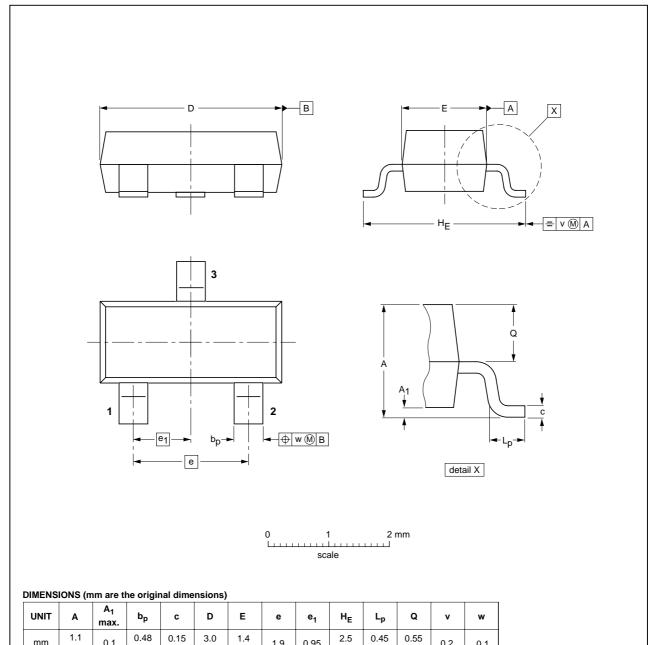
# NPN high voltage transistor

**BSS64** 

#### **PACKAGE OUTLINE**

#### Plastic surface mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	IEC JEDEC EIAJ PROJECTION		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				<del>97-02-28</del> 99-09-13

0.2

0.1

0.95

1.9

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0.9

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### NPN high voltage transistor

**BSS64** 

#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### **DEFINITIONS**

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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